Silicon NPN Power Transistors 2SC3297

DESCRIPTION

- With TO-220Fa package
- Low saturation voltage
- High speed switching time

APPLICATIONS

- High current switching applications

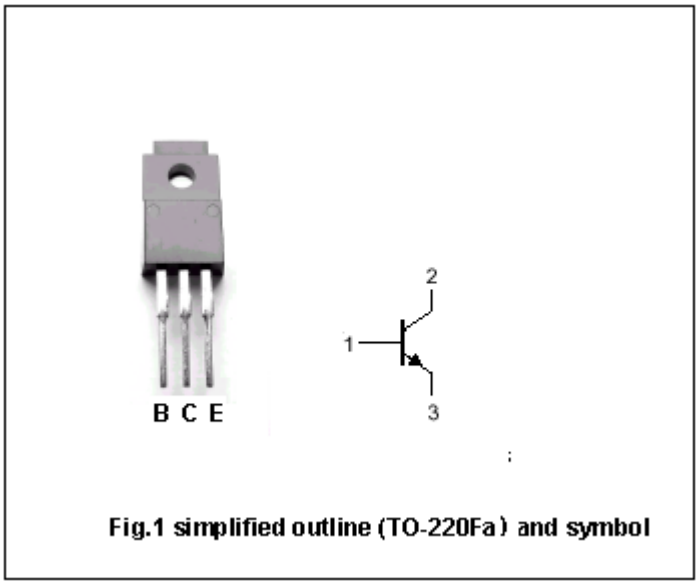

Fig.1 simplified outline (TO-220Fa) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	30	V
V_{CEO}	Collector-emitter voltage	Open base	30	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		3	A
P_C	Collector power dissipation	T_C=25℃	15	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-emitter breakdown voltage	I_C=10mA , I_B=0	30			V
V_{CBO}	Collector-base breakdown voltage	I_C=1mA , I_E=0	30			V
V_{EBO}	Emitter-base breakdown voltage	I_E=1mA , I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2A ;I_B=0.2A			1.0	V
V_{BE}	Base-emitter on voltage	I_C=0.5A ; V_{CE}=5V			1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=30V; I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			10	μA
h_{FE-1}	DC current gain	I_C=0.5A ; V_{CE}=2V	70		280	
h_{FE-2}	DC current gain	I_C=3A ; V_{CE}=5V	20			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=5V		100		MHz

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PACKAGE OUTLINE

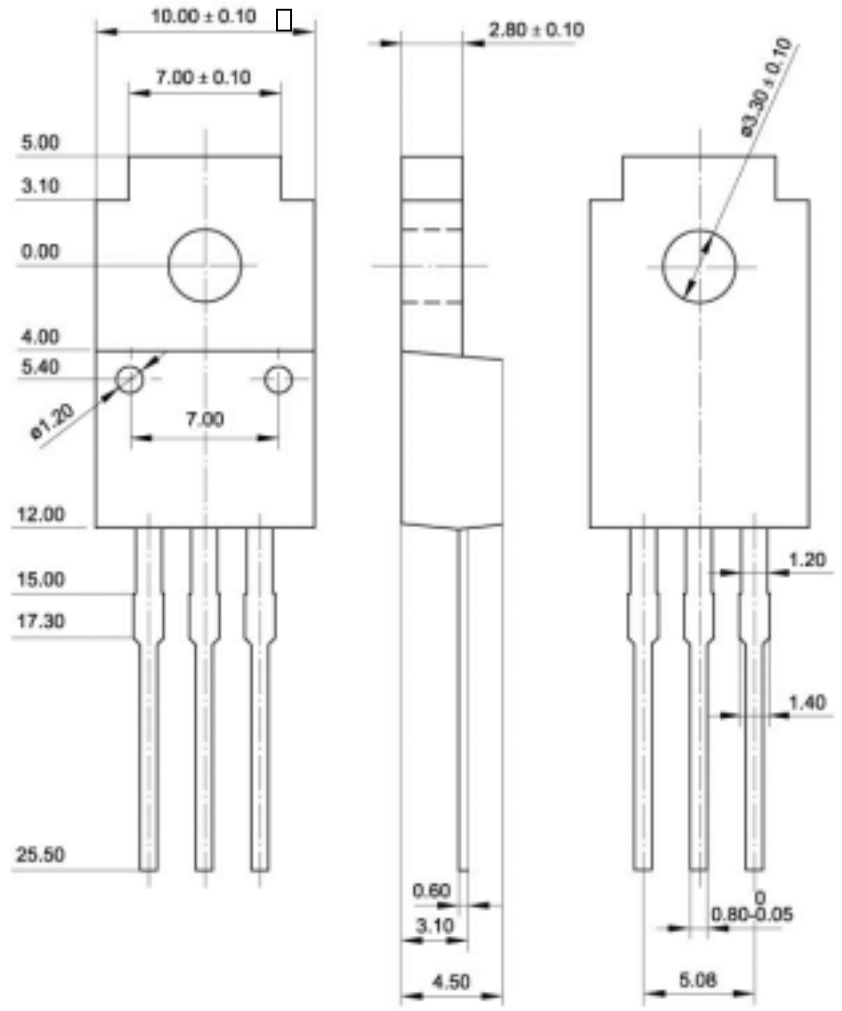

Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)